

N-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}(\Omega)$	I _D (A)		
20	0.0035 at $V_{GS} = 4.5 \text{ V}$	25		
	0.0047 at V _{GS} = 2.5 V	20		

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Top View

Ordering Information: Si4864DY-T1-E3 (Lead (Pb)-free) Si4864DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

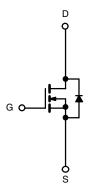
FEATURES

- Halogen-free According to IEC 61249-2-21 Available
- TrenchFET® Power MOSFETs: 2.5 V Rated
- Low 3.5 m Ω R_{DS(on)}
- PWM (Q_{gd} and R_g) Optimized



APPLICATIONS

• Low-Side MOSFET in Synchronous Buck DC/DC Converters in Servers and Routers



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	20		V
Gate-Source Voltage		V _{GS}	± 8		V
O-ations David O-and (T., 150.00)	T _A = 25 °C	- I _D	25	17	
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C		20	13	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	2.9	1.3	
M	T _A = 25 °C	P _D	3.5	1.6	W
Maximum Power Dissipation ^a	T _A = 70 °C] 'D	2.2	1	VV
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 t	o 150	°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Manipular Landian La Anglianda	t ≤ 10 s	R _{thJA}	29	35	
Maximum Junction-to-Ambient ^a	Steady State	' 'thJA	67	80	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	13	16	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.

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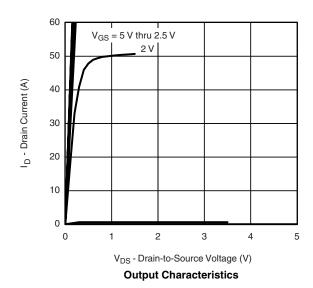
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6		2	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 8 \text{ V}$			± 100	nA	
Zava Cata Valtaga Drain Current	1	V _{DS} = 20 V, V _{GS} = 0 V			1	μΑ	
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 4.5 \text{ V}$	30			Α	
	В	$V_{GS} = 4.5 \text{ V}, I_D = 25 \text{ A}$		0.0028	0.0035	Ω	
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 2.5 \text{ V}, I_D = 20 \text{ A}$		0.0038	0.0047		
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 6 \text{ V}, I_{D} = 25 \text{ A}$		70		S	
Diode Forward Voltage ^a	V_{SD}	$I_S = 2.9 \text{ A}, V_{GS} = 0 \text{ V}$		0.70	1.1	٧	
Dynamic ^b				•	1		
Total Gate Charge	Qg			47	70		
Gate-Source Charge	Q _{gs}	$V_{DS} = 10 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 25 \text{ A}$		10		nC	
Gate-Drain Charge	Q_{gd}			13.4			
Gate Resistance	R_g		0.5	1.5	2.6	Ω	
Turn-On Delay Time	t _{d(on)}			40	60		
Rise Time	t _r	V_{DD} = 10 V, R_L = 10 Ω		44	65		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 4.5 V, R_g = 6 Ω		150	240	ns	
Fall Time	t _f			72	110		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = 2.9 A, dI/dt = 100 A/μs		57	80		

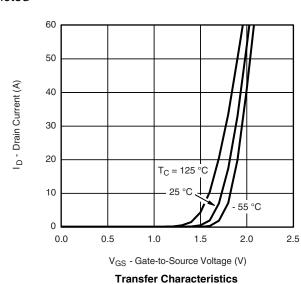
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

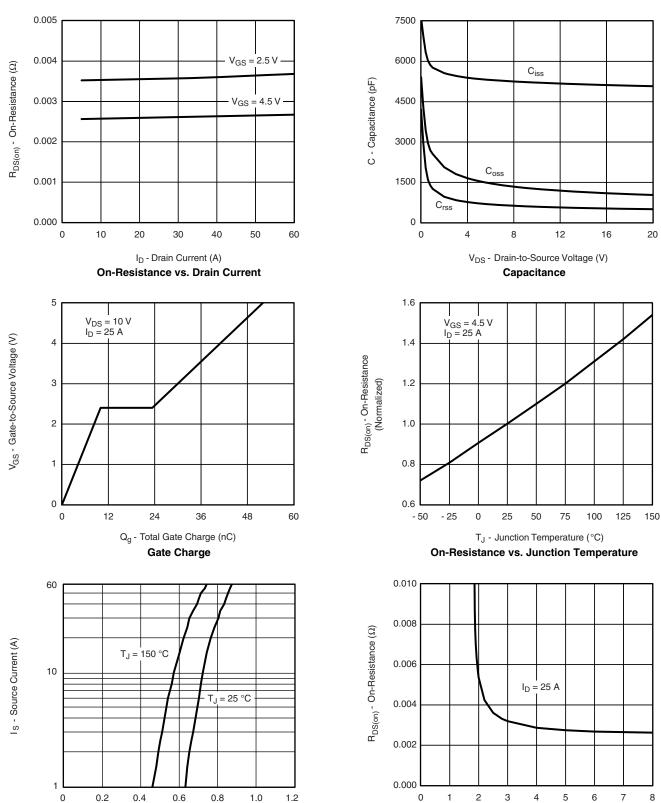








TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



0

0.2

0.4

0.6

V_{SD} - Source-to-Drain Voltage (V)

Source-Drain Diode Forward Voltage

0.8

1.0

1.2

0

2

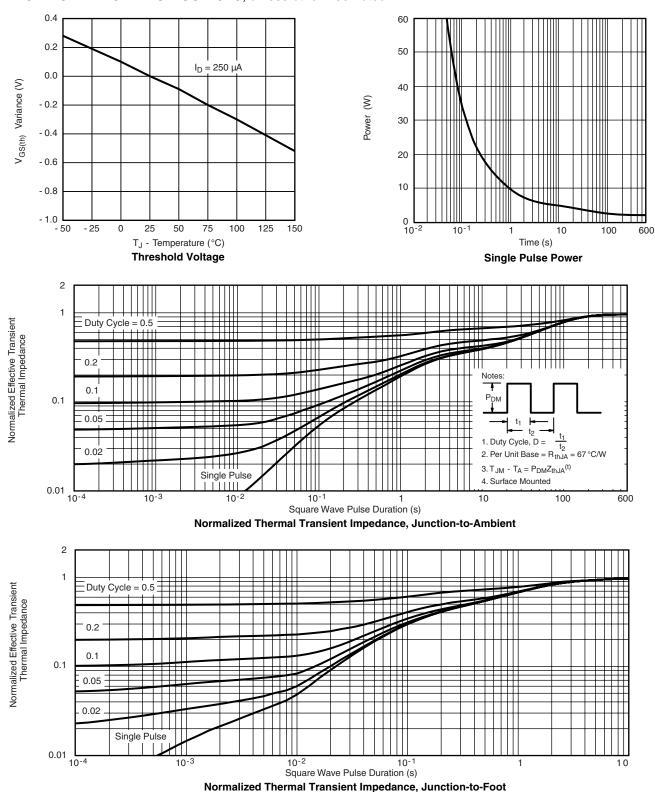
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V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage

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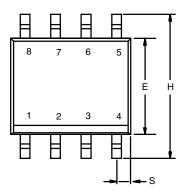
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



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SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012







	MILLIMETERS INCHES			HES		
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
Е	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050) BSC		
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
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RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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